L Number	Hits	Search Text	DB	Time stamp
3	4	("4336489").PN.	USPAT;	2002/10/06
	_		US-PGPUB; EPO; JPO; DERWENT;	10:34
-	0	("salicide").PN.	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/03/05 17:00
-	2475	salicide	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/03/05 17:08
-	431	salicide.ti.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/05
-	229	(257/173).ccls.	IBM_TDB USPAT; US-PGPUB	2002/10/04
-	322	(257/339).CCLS.	USPAT; US-PGPUB	2002/10/04
	725	(257/355).CCLS.	USPAT; US-PGPUB	2002/10/04
_	1186	((257/173).CCLS.) or ((257/339).CCLS.) or ((257/355).CCLS.)	USPAT; US-PGPUB; EPO; JPO;	2002/10/04 12:05
-	18	(((257/173).CCLS.) or ((257/339).CCLS.) or ((257/355).CCLS.)) and (mos or mosfet or nmos or nmosfet or pmos or pmosfet or cmos or cmosfet) and protect\$3 and	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/04 13:58
_	18	silicide and zener (US-6307238-\$ or US-6281527-\$ or US-6268639-\$ or US-6175139-\$ or US-6121665-\$ or US-5939767-\$ or US-5910675-\$ or US-5708288-\$ or US-5683918-\$ or US-5623387-\$ or US-5543650-\$ or US-5229633-\$ or US-5166089-\$ or US-5128730-\$ or US-4509089-\$ or US-6365941-\$).did. or (US-20020096722-\$ or	IBM_TDB USPAT; US-PGPUB	2002/10/04 13:29
_	132	US-20020030231-\$).did. (((257/173).CCLS.) or ((257/339).CCLS.) or ((257/355).CCLS.)) and (mos or mosfet or nmos or nmosfet or pmos or pmosfet or cmos or cmosfet) and zener	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/04 14:07
-	30	((257/288).CCLS.) and second near3 diffusion	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/04 14:16
_	7	((257/288).CCLS.) and double-diffused	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/04 14:17
_	. 11	((257/288).CCLS.) and double adj diffused	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/04 14:18

	788	(257/288).CCLS.	USPAT;	2002/10/04
ļ ⁻	/88	(231/200).CCLS.	US-PGPUB;	2002/10/04
				14:31
			EPO; JPO;	1
			DERWENT;	
	·		IBM_TDB	
-	8	(US-6025628-\$ or US-6307224-\$ or	USPAT;	2002/10/04
		US-4509089-\$ or US-5166089-\$ or	US-PGPUB;	19:04
		US-6268639-\$ or US-5623387-\$).did. or	JPO	
		(US-20020030231-\$).did. or		
		(JP-06204475-\$).did.		
_	8	((US-6025628-\$ or US-6307224-\$ or	USPAT;	2002/10/04
		US-4509089-\$ or US-5166089-\$ or	US-PGPUB;	19:18
		US-6268639-\$ or US-5623387-\$).did. or	EPO; JPO;	
		(US-20020030231-\$).did. or	DERWENT;	
		(JP-06204475-\$).did.)	IBM TDB	
	463		USPAT;	2002/10/04
_	403	esd	US-PGPUB;	19:19
		esa		19.19
			EPO; JPO;	
			DERWENT;	
	0.50		IBM_TDB	0000/10/04
_	268		USPAT;	2002/10/04
		esd and 257/\$6.ccls.	US-PGPUB;	19:19
}			EPO; JPO;	1
1			DERWENT;	
			IBM_TDB	
-	112	(well same protect\$3 same substrate same	USPAT;	2002/10/04
		esd and 257/\$6.ccls.) and well near4	US-PGPUB;	19:20
		protect\$3	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	37	(well same protect\$3 same substrate same	USPAT;	2002/10/04
		esd and 257/\$6.ccls.) and well near4	US-PGPUB;	19:21
		protect\$3.ti,ab,clm.	EPO; JPO;	
1			DERWENT;	
			IBM TDB	
_	12	(well same protect\$3 same substrate same	USPAT;	2002/10/04
]	12	esd and 257/\$6.ccls.) and well near4	US-PGPUB;	19:22
]		protect\$3.ti,ab,clm. and (mos or	EPO; JPO;	1
		mosfet).ti,ab,clm. and (mos of	DERWENT;	
i		mosiec, . ci, ab, cim.	IBM TDB	
L	l		T DIA T D D	